APM4532

Dual Enhancement Mode MOSFET (N-and P-Channel)

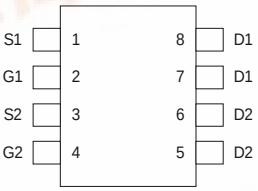
Features

- N-Channel
  30V/5A, $R_{DS(ON)}$=35mΩ(typ.) @ V_{GS}=10V
  $R_{DS(ON)}$=60mΩ(typ.) @ V_{GS}=4.5V
- P-Channel
  -30V/-3.5A, $R_{DS(ON)}$=85mΩ(typ.) @ V_{GS}=-10V
  $R_{DS(ON)}$=135mΩ(typ.) @ V_{GS}=-4.5V
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- SO-8 Package

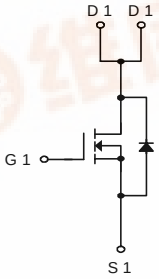
Applications

- Power Management in Notebook Computer , Portable Equipment and Battery Powered Systems.

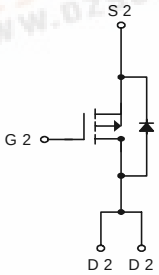
Pin Description



SO-8



N-Channel MOSFET



P-Channel MOSFET

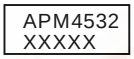
Ordering and Marking Information

APM4532 □□-□□

- Handling Code
- Temp. Range
- Package Code

Package Code
K : SO-8
Operation Junction Temp. Range
C : -55 to 150°C
Handling Code
TR : Tape & Reel

APM4532 K :



XXXXX - Date Code

Absolute Maximum Ratings (T$_A$ = 25°C unless otherwise noted)

Symbol	Parameter		N-Channel	P-Channel	Unit
V_{DSS}	Drain-Source Voltage		30	-30	V
V_{GSS}	Gate-Source Voltage		±25	±25	
I_D*	Maximum Drain Current – Continuous		5	-3.5	A
I_{DM}	Maximum Drain Current – Pulsed		20	-20	
P_D	Maximum Power Dissipation	T_A=25°C	2	2	W
		T_A=100°C	0.8	0.8	
T_J	Maximum Junction Temperature		150		°C
T_{STG}	Storage Temperature Range		-55 to 150		°C
$R_{\theta jA}$	Thermal Resistance – Junction to Ambient		62.5		°C/W

* Surface Mounted on FR4 Board, t ≤ 10 sec.

Electrical Characteristics (T$_A$ = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition		APM4532 Min.	APM4532 Typ.	APM4532 Max.	Unit
Static							
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_{DS}=250µA	N-Ch	30			V
			P-Ch	-30			
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V , V_{GS}=0V	N-Ch			1	µA
		V_{DS}=-24V , V_{GS}=0V	P-Ch			-1	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_{DS}=250µA	N-Ch	1	1.5	2	V
		V_{DS}=V_{GS} , I_{DS}=-250µA	P-Ch	-1	-1.5	-2	
I_{GSS}	Gate Leakage Current	V_{GS}=±25V , V_{DS}=0V	N-Ch			±100	nA
			P-Ch			±100	
$R_{DS(ON)}$[a]	Drain-Source On-state Resistance	V_{GS}=10V , I_{DS}=5A	N-Ch		35	45	mΩ
		V_{GS}=4.5V , I_{DS}=4A			60	70	
		V_{GS}=-10V , I_{DS}=-3.5A	P-Ch		85	95	
		V_{GS}=-4.5V , I_{DS}=-2.5A			135	150	
V_{SD}[a]	Diode Forward Voltage	I_{SD}=1.7A , V_{GS}=0V	N-Ch		0.7	1.3	V
		I_{SD}=-1.7A , V_{GS}=0V	P-Ch		-0.7	-1.3	

Notes

[a] : Pulse test ; pulse width ≤300µs, duty cycle ≤ 2%

Electrical Characteristics (Cont.) (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition		APM4532			Unit
				Min.	Typ.	Max.	
Dynamic[a]							
Q_g	Total Gate Charge	N-Channel	N-Ch		7	15	nC
		V_{DS}=10V , I_{DS}= 5A	P-Ch		8	15	
Q_{gs}	Gate-Source Charge	V_{GS}=4.5V	N-Ch		4.7		
		P-Channel	P-Ch		2		
Q_{gd}	Gate-Drain Charge	V_{DS}=-10V , I_{DS}=-3.5A	N-Ch		1.1		
		V_{GS}=-4.5V	P-Ch		1		
$t_{d(ON)}$	Turn-on Delay Time	N-Channel	N-Ch		10	15	ns
		V_{DD}=10V , I_{DS}=1A ,	P-Ch		8	15	
T_r	Turn-on Rise Time	V_{GEN}=4.5V , R_G=10Ω	N-Ch		8	20	
			P-Ch		7	20	
$t_{d(OFF)}$	Turn-off Delay Time	P-Channel	N-Ch		20	28	
		V_{DD}=-10V , I_{DS}=-1A ,	P-Ch		15	28	
T_f	Turn-off Fall Time	V_{GEN}=-4.5V , R_G=10Ω	N-Ch		5	15	
			P-Ch		7	18	
C_{iss}	Input Capacitance		N-Ch		376		pF
		V_{GS}=0V	P-Ch		495		
C_{oss}	Output Capacitance	V_{DS}=15V	N-Ch		115		
		Frequency=1.0MHz	P-Ch		130		
C_{rss}	Reverse Transfer Capacitance		N-Ch		58		
			P-Ch		60		

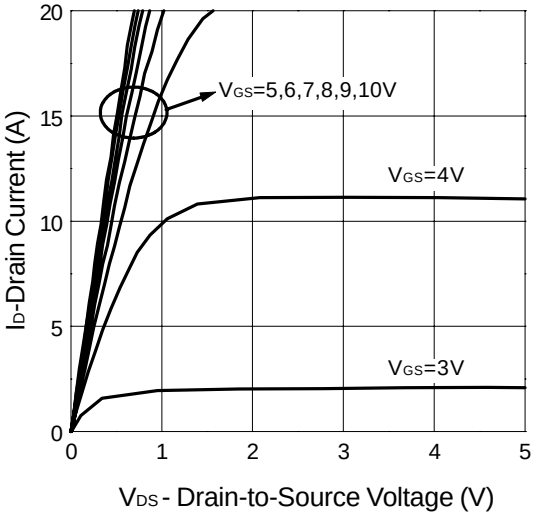
Notes

[a] : Guaranteed by design, not subject to production testing

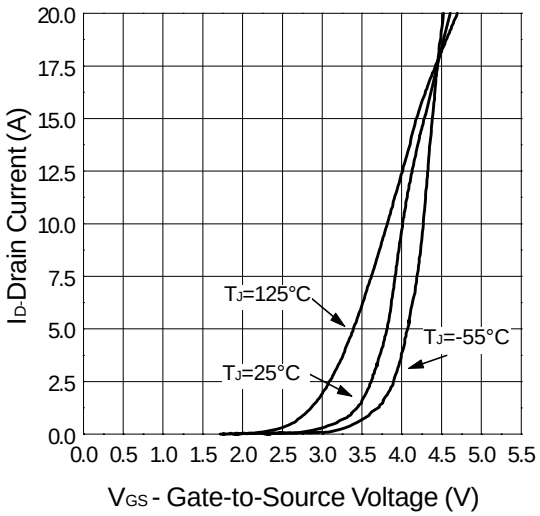
Typical Characteristics

N-Channel

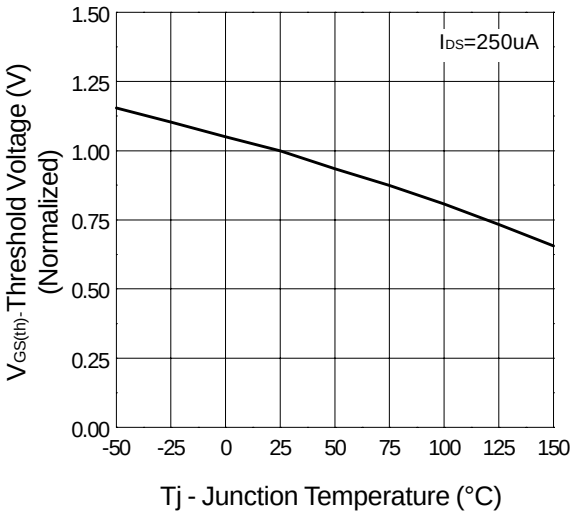
Output Characteristics



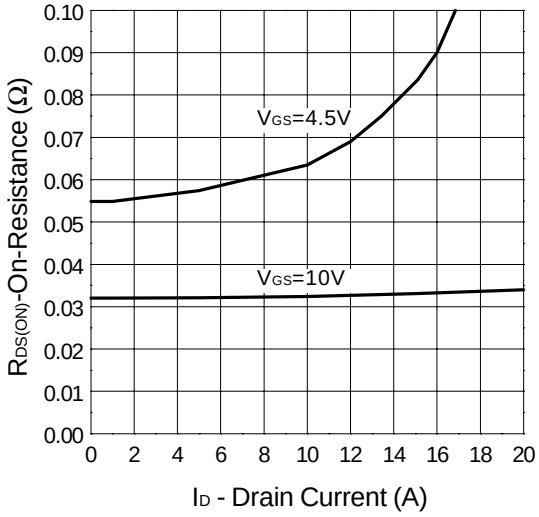
Transfer Characteristics



Threshold Voltage vs. Junction Temperature



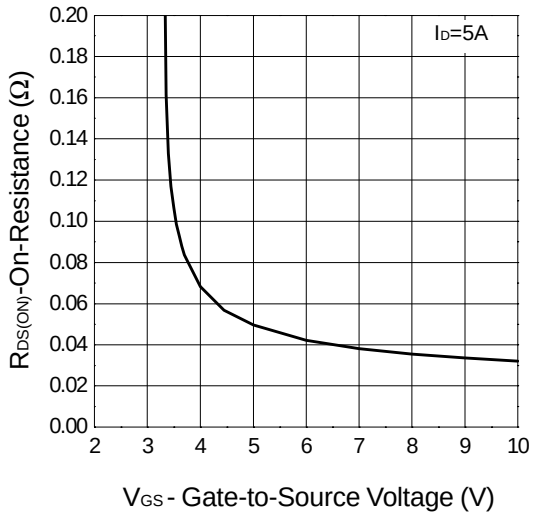
On-Resistance vs. Drain Current



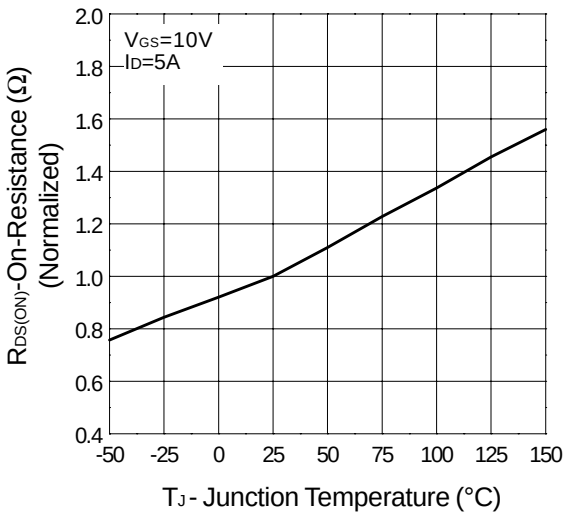
Typical Characteristics (Cont.)

N-Channel

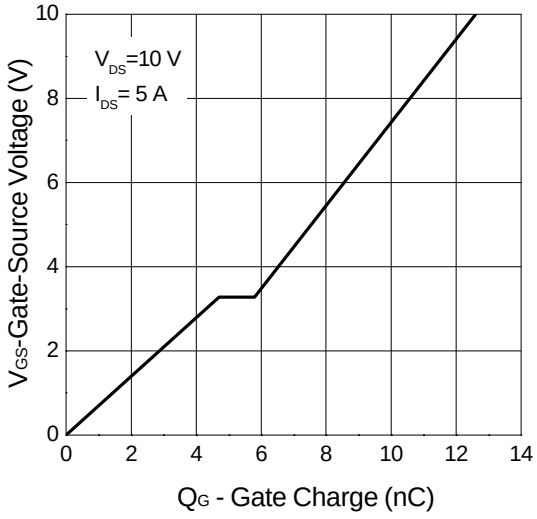
On-Resistance vs. Gate-to-Source Voltage



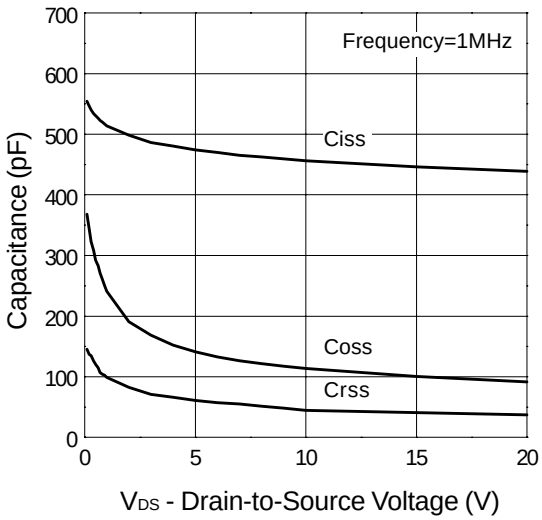
On-Resistance vs. Junction Temperature



Gate Charge



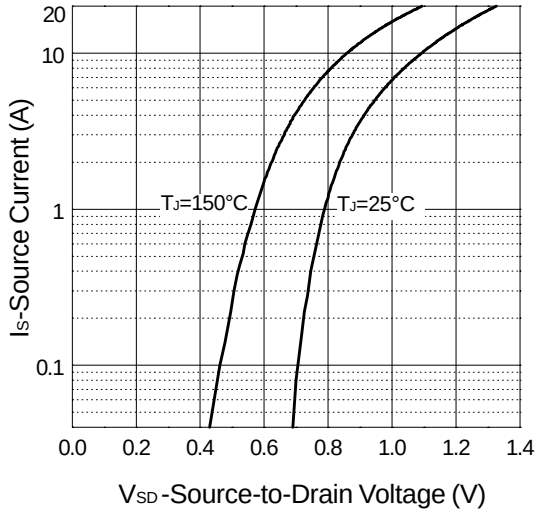
Capacitance



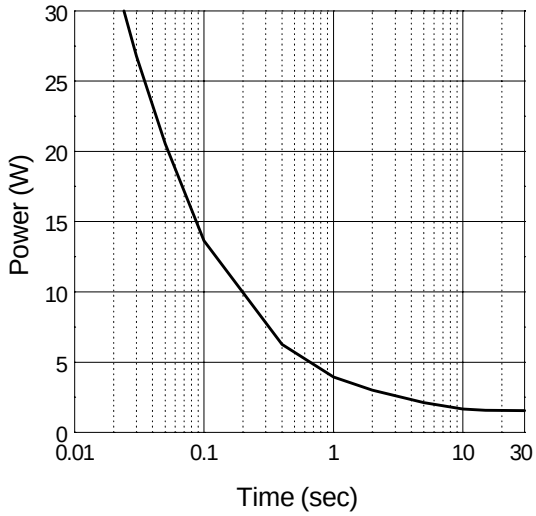
Typical Characteristics (Cont.)

N-Channel

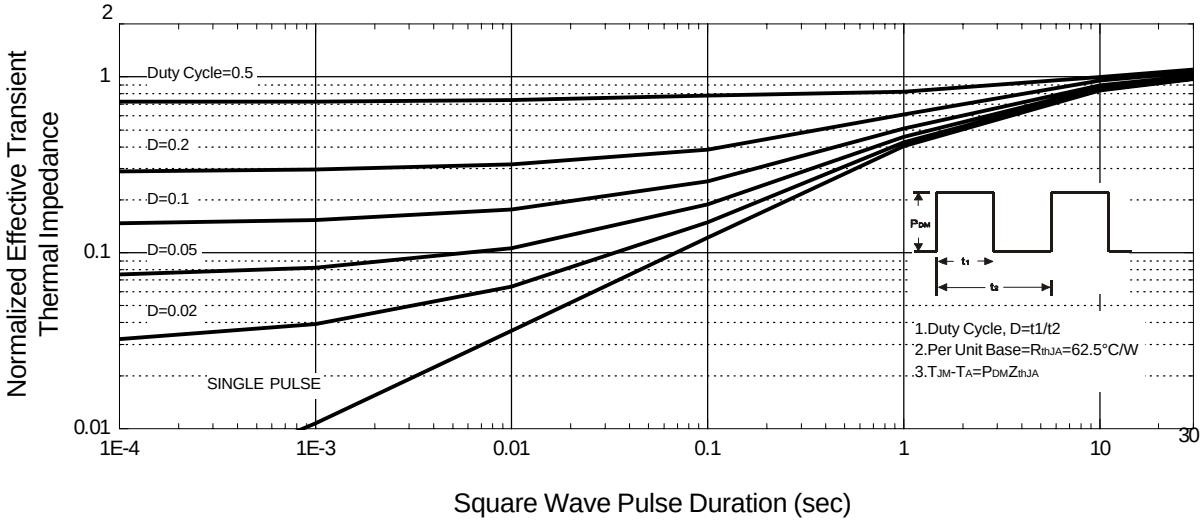
Source-Drain Diode Forward Voltage



Single Pulse Power



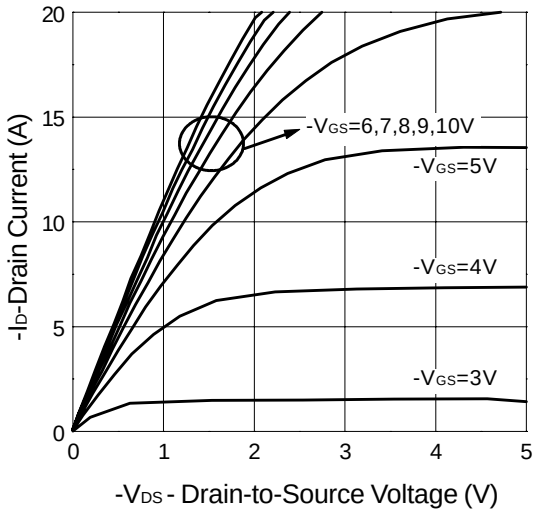
Normalized Thermal Transient Impedence, Junction to Ambient



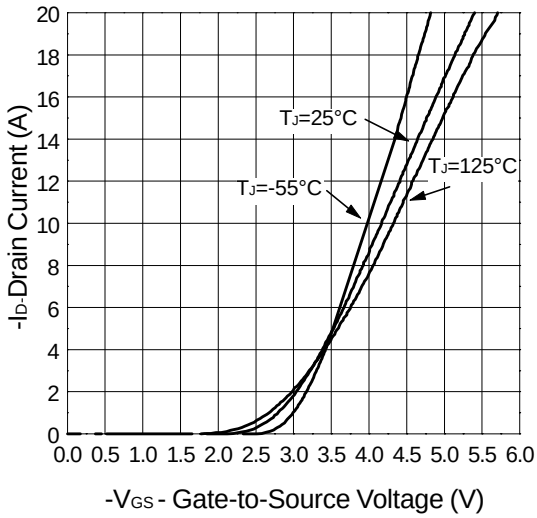
Typical Characteristics

P-Channel

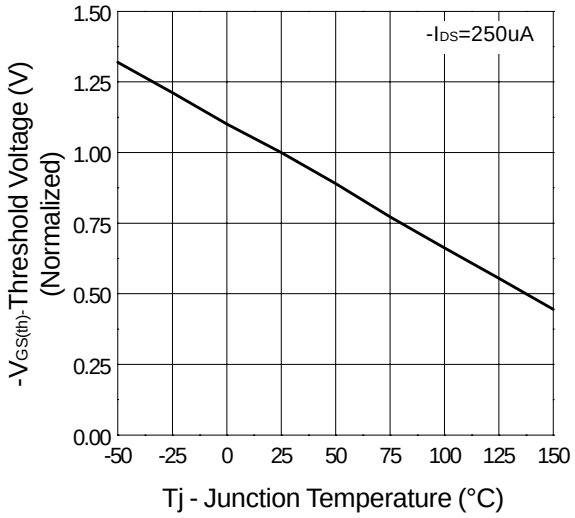
Output Characteristics



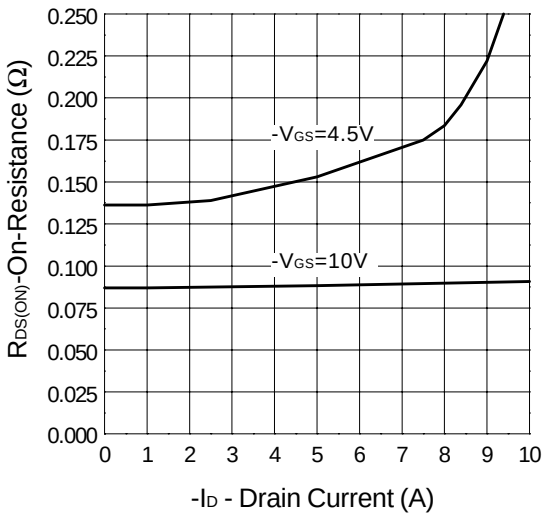
Transfer Characteristics



Threshold Voltage vs. Junction Temperature



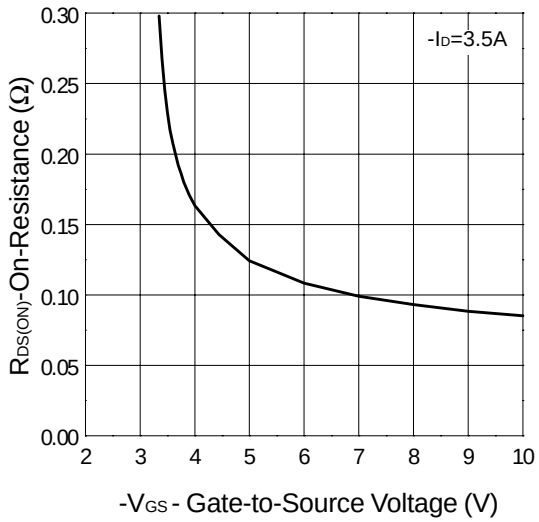
On-Resistance vs. Drain Current



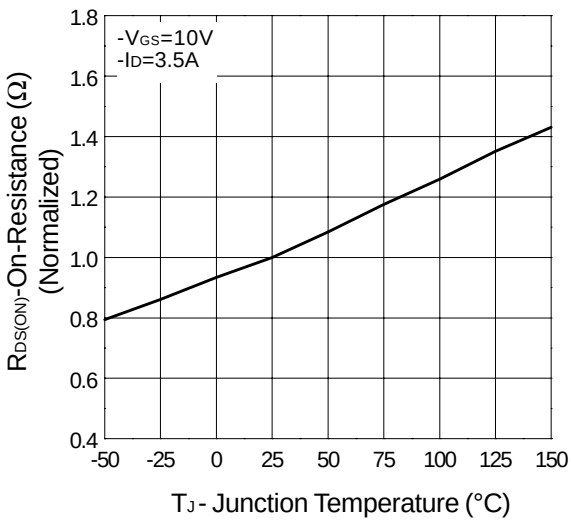
Typical Characteristics (Cont.)

P-Channel

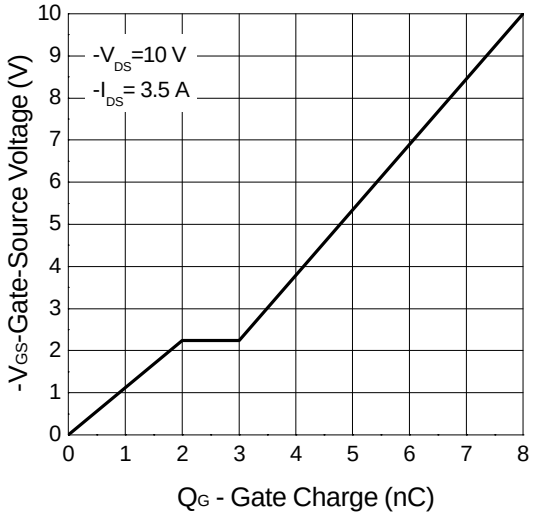
On-Resistance vs. Gate-to-Source Voltage



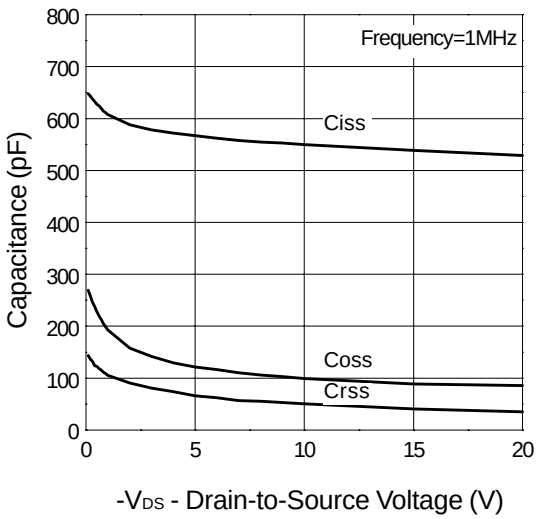
On-Resistance vs. Junction Temperature



Gate Charge



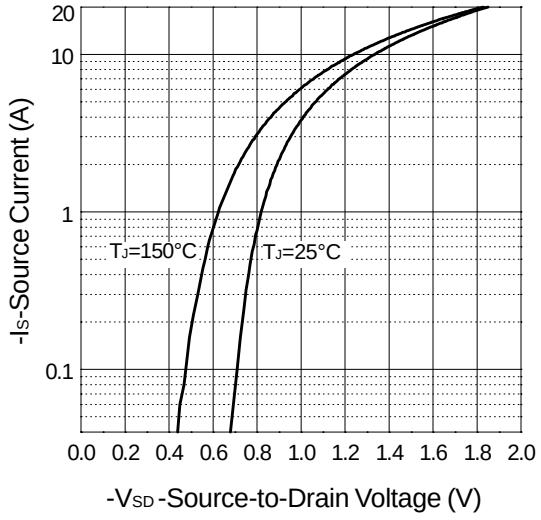
Capacitance



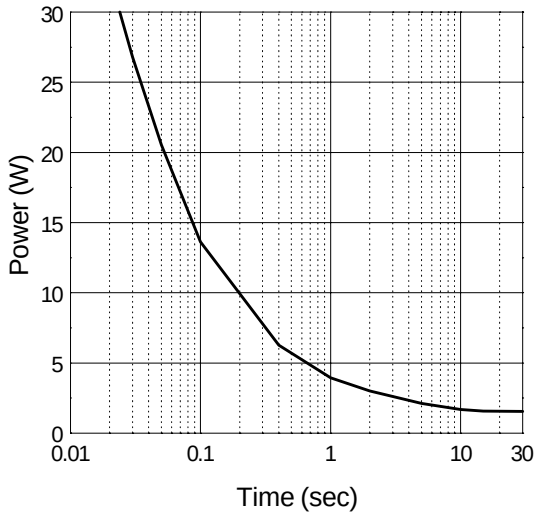
Typical Characteristics (Cont.)

P-Channel

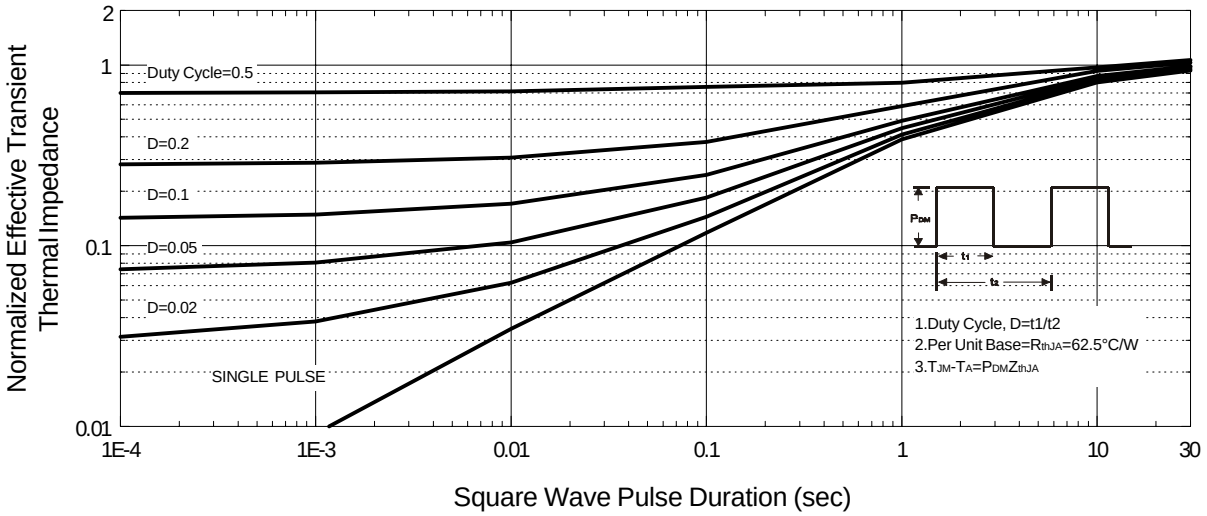
Source-Drain Diode Forward Voltage



Single Pulse Power

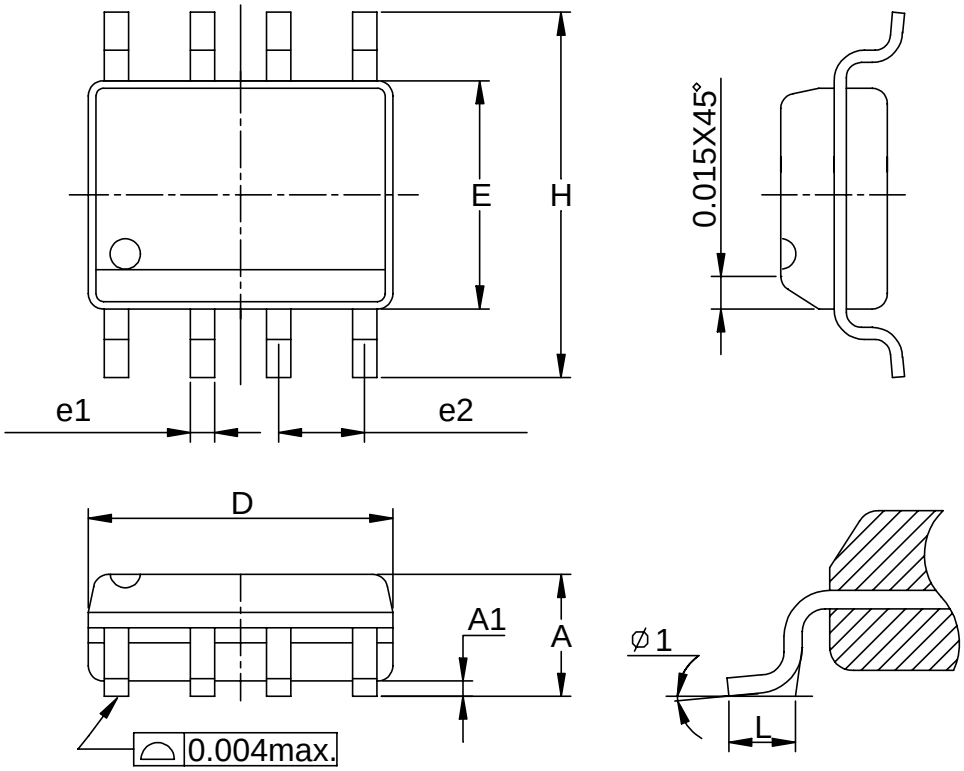


Normalized Thermal Transient Impedence, Junction to Ambient



Packaging Information

SOP-8 pin (Reference JEDEC Registration MS-012)



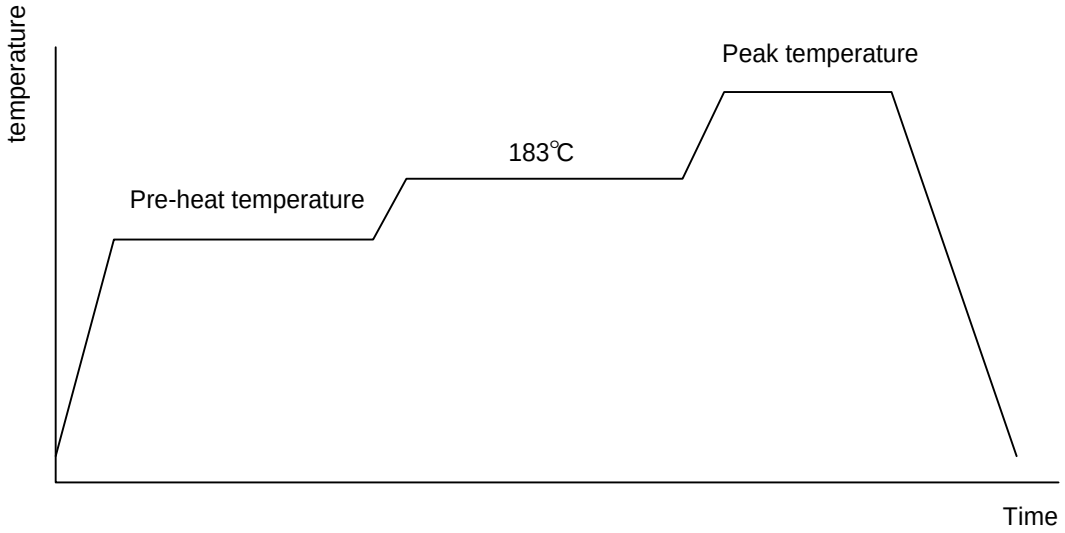
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	5.00	0.189	0.197
E	3.80	4.00	0.150	0.157
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
e1	0.33	0.51	0.013	0.020
e2	1.27BSC		0.50BSC	
ϕ 1	8°		8°	

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)

Reference JEDEC Standard J-STD-020A APRIL 1999



Classification Reflow Profiles

	Convection or IR/ Convection	VPR
Average ramp-up rate(183°C to Peak)	3°C/second max.	10 °C /second max.
Preheat temperature 125 ± 25°C)	120 seconds max	
Temperature maintained above 183°C	60 – 150 seconds	
Time within 5°C of actual peak temperature	10 –20 seconds	60 seconds
Peak temperature range	220 +5/-0°C or 235 +5/-0°C	215-219°C or 235 +5/-0°C
Ramp-down rate	6 °C /second max.	10 °C /second max.
Time 25°C to peak temperature	6 minutes max.	

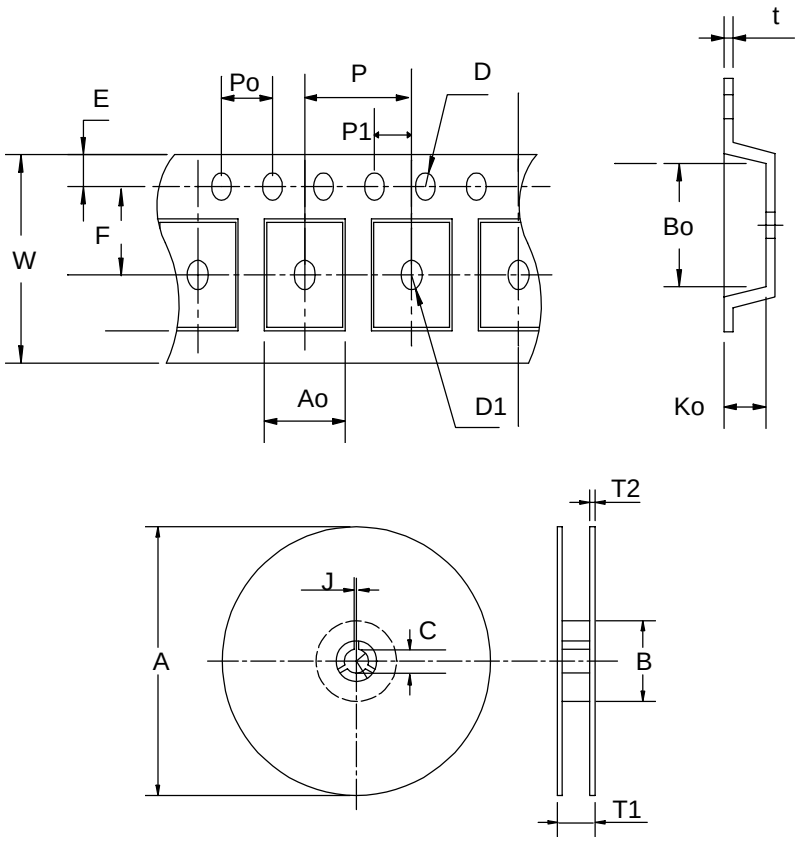
Package Reflow Conditions

pkg. thickness ≥ 2.5mm and all bgas	**pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm³**	**pkg. thickness < 2.5mm and pkg. volume < 350mm³**
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C

Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C,5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
SOP- 8	330 ± 1	62 +1.5	12.75+ 0.15	2 ± 0.5	12.4 ± 0.2	2 ± 0.2	12± 0. 3	8± 0.1	1.75±0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5± 1	1.55 +0.1	1.55+ 0.25	4.0 ± 0.1	2.0 ± 0.1	6.4 ± 0.1	5.2± 0. 1	2.1± 0.1	0.3±0.013

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOP- 8	12	9.3	2500

Customer Service

Anpec Electronics Corp.
Head Office :
5F, No. 2 Li-Hsin Road, SBIP,
Hsin-Chu, Taiwan, R.O.C.
Tel : 886-3-5642000
Fax : 886-3-5642050
Taipei Branch :
7F, No. 137, Lane 235, Pac Chiao Rd.,
Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.
Tel : 886-2-89191368
Fax : 886-2-89191369